LETTER TO THE EDITOR

NOTE ON THE ELECTRON SCREENING FUNCTION AT LOW TEMPE-RATURES

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Received 21 July 1973

In evaluating the screening function in metals it is useful to approximate the actual one-electron energy by an analytically simple function of the wave number $^{1-5}$. The approach which is widely used assumes that the energy is a quadratic function of the wave number. In an earlier paper this approximation was applied to the calculation of temperature effects in the dynamical screening function in degenerate semiconductors⁶. The aim of the present note is to improve this calculation by including the exchange and correlation contributions to the energy.

To determine the lowest-order temperature contribution to the screening function, it suffices to start from the T = 0 expression for energy. In the scheme of Bohm and Pines⁷, the Hartree-Fock energy of an electron the wave number of which lies in the range $k_F - k_c is⁸$

$$E = \frac{\hbar^2 p^2}{2m} - \frac{e^2}{2\pi \epsilon} \left(k_F - 2k_e + \frac{k_F^2 - p^2}{p} \ln \frac{k_F + p}{k_e} + \frac{3}{2} p + \frac{k_e^2 - k_F^2}{2p} \right), \quad (1)$$

where ε is the dielectric constant of the media, while k_F and k_c are the Fermi and the cut-off wave number, respectively. With the help of (1) we arrive at the expression for the concentration

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$$N = \frac{1}{3\pi^{2}} \left[p_{\mu}^{3} + \frac{(\pi KT)^{2}}{6} \left(\frac{d^{2}}{dE^{2}} p^{3} \right)_{\mu} \right] =$$

$$= \frac{p_{\mu}^{3}}{3\pi^{2}} \left\{ 1 + \frac{\pi^{2}}{8} \left(\frac{T}{T_{F}} \right)^{2} \frac{1 - \gamma \left(\frac{7}{2} - \beta^{2} - 3 \ln \frac{2}{\beta} \right)}{\left[1 - \gamma \left(1 - \frac{\beta^{2}}{4} - 1 \ln \frac{2}{\beta} \right) \right]^{3}} \right\}.$$
(2)

Here we defined $\beta = k_c/k_F$, $T_F = \hbar^2 k_F^2/2mK$ and $\gamma = (4/9\pi^4)^{1/3} r_s$, with $r_s = (9\pi/4)^{1/3} me^2/\hbar^2 \epsilon k_F$. After comparing (2) with $N = k_F^3/3\pi^2$, it follows

$$p_{\mu} = k_F \left\{ 1 - \frac{\pi^2}{24} \left(\frac{T}{T_F} \right)^2 \frac{1 - \gamma \left(\frac{7}{2} - \beta^2 - 3 \ln \frac{2}{\beta} \right)}{\left[1 - \gamma \left(1 - \frac{\beta^2}{4} - \ln \frac{2}{\beta} \right) \right]^3} \right\}.$$
 (3)

In the limiting case, when electron exchange is neglected ($\gamma = 0$), relation (3) leads, of course, to the well-known expression for the chemical potential of an ideal Fermi gas $\mu = \mu(0) (1 - \pi^2 T^2/12T_p^2)$.

Table

Repeating the same procedure as in deriving expression (3), after a tedious but straightforward calculation, for the real part of the high-frequency long-wavelength electron polarizability we find

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$$4\pi \alpha(k, \omega) = -\frac{\omega_{p}^{2}}{\omega^{2}} \left\{ 1 + \frac{3k^{2}}{5\omega^{2}} \upsilon_{p}^{2} \left[1 - \gamma \left(1 + \frac{\beta^{2}}{4} - \frac{\beta^{4}}{8} \right) + \frac{5\pi^{2}}{12} \left(\frac{T}{T_{F}} \right)^{2} Z \right] \right\}.$$
 (4)

In (4), ω_p is the classical plasma frequency and Z is given by

$$Z = \frac{1}{\left[1 - \gamma \left(1 - \frac{\beta^2}{4} - \ln \frac{2}{\beta}\right)\right]^3} \left\{1 + \gamma \left(-\frac{9}{10} + \frac{4}{15}\beta^2 + \frac{17}{15}\ln \frac{2}{\beta}\right) - \frac{\gamma^2}{15} \left[\frac{3}{2} - \frac{\beta^2}{8} - \frac{\beta^4}{16} + \left(\frac{1}{2} - \frac{3\beta^2}{4} - 2\ln \frac{2}{\beta}\right)\ln \frac{2}{\beta}\right]\right\}.$$
 (5)

Expression (5) has to be compared with the value calculated in the approximation that the electron energy is equal to $\hbar^2 p^2/2m^{6}$

$$Z_0 = 1 + \frac{\gamma}{10} \left(1 + \frac{\beta^2}{6} + \frac{4}{3} \ln \frac{2}{\beta} \right).$$
 (6)

The numerical calculation is performed by choosing for β the following values: $\beta_1 = 0.353 \sqrt{r_s^{9}}, \beta_2 = 0.470 \sqrt{r_s^{10}}$ and β_3 determined by ^{11,12}

$$\left(1 + \frac{\beta_3}{2}\right) \ln \left(1 + \frac{2}{\beta_3}\right) = 1 + \frac{\beta_3^2}{2\gamma}.$$
 (7)

As can be seen from the Table, the choice of β has no essential influence on the behaviour of both Z_0 and Z. This refers particularly to the region $r_s \leq 1$, where we expect the non-RPA contributions to be small. In all the three cases Z_0 is a monotonously increasing function of β , while Z has a small drop in the region of high densities with a minimum in the vicinity of $r_s = 1$. In spite of that, the numerical values obtained in these two approaches differ for $r_s \leq 5$ by no more than 20%.

It is somewhat surprising that even in the high-density limit, the deviation of Z from the RPA value $Z_{RPA} = 1$ is not negligible. This is the consequence of the logarithmic dependence of Z on β . Nevertheless, this deviation is not large, showing

that the effect of electron exchange and correlation does not appreciably modify T^2 term in the screening function.

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